



LDMOS FIELD EFFECT TRANSISTOR

NE55410GR

N-CHANNEL SILICON POWER LDMOS FET FOR 2 W + 10 W VHF to L-BAND SINGLE-END POWER AMPLIFIER

DESCRIPTION

The NE55410GR is an N-channel enhancement-mode LDMOS FET designed for driver 0.1 to 2.6 GHz PA, such as, cellular base station amplifier, analog/digital TV-transmitters, and the other PA's. This product has two different FET's on one die manufactured using our NEWMOS technology (our WSi gate lateral MOS FET), and its nitride surface passivation and quadruple layer aluminum silicon metalization offer a high degree of reliability.

FEATURES

- Two different FET's (Q1 : $P_{out} = 2\text{ W}$, Q2 : $P_{out} = 10\text{ W}$) in one package
- ★ • Over 25 dB gain available by connecting two FET's in series
- ★ : $G_L(Q1) = 13.5\text{ dB TYP.}$ ($V_{DS} = 28\text{ V}$, $I_{Dset}(Q1) = 20\text{ mA}$, $f = 2\text{ 140 MHz}$)
- ★ : $G_L(Q2) = 11.0\text{ dB TYP.}$ ($V_{DS} = 28\text{ V}$, $I_{Dset}(Q2) = 100\text{ mA}$, $f = 2\text{ 140 MHz}$)
- ★ • High 1 dB compression output power : $P_{O(1\text{ dB})}(Q1) = 35.4\text{ dBm TYP.}$ ($V_{DS} = 28\text{ V}$, $I_{Dset}(Q1) = 20\text{ mA}$, $f = 2\text{ 140 MHz}$)
- ★ : $P_{O(1\text{ dB})}(Q2) = 40.4\text{ dBm TYP.}$ ($V_{DS} = 28\text{ V}$, $I_{Dset}(Q2) = 100\text{ mA}$, $f = 2\text{ 140 MHz}$)
- ★ • High drain efficiency : $\eta_d(Q1) = 52\% \text{ TYP.}$ ($V_{DS} = 28\text{ V}$, $I_{Dset}(Q1) = 20\text{ mA}$, $f = 2\text{ 140 MHz}$)
- ★ : $\eta_d(Q2) = 46\% \text{ TYP.}$ ($V_{DS} = 28\text{ V}$, $I_{Dset}(Q2) = 100\text{ mA}$, $f = 2\text{ 140 MHz}$)
- ★ • Low intermodulation distortion : $IM_3(Q1) = -40\text{ dBc TYP.}$ ($V_{DS} = 28\text{ V}$, $I_{Dset}(Q1+Q2) = 120\text{ mA}$, $f = 2\text{ 132.5/2 147.5 MHz}$, $P_{out} = 33\text{ dBm (2 tones)}$)
- Single Supply ($V_{bs} : 3\text{ V} < V_{DS} \leq 30\text{ V}$)
- Excellent Thermal Stability
- Surface mount type and Super low cost plastic package : 16-pin plastic HTSSOP
- Integrated ESD protection
- Excellent stability against HCI (Hot Carrier Injection)

APPLICATION

- Digital cellular base station PA : W-CDMA/GSM/D-AMPS/PDC/N-CDMA/PCS etc.
- UHF-band TV transmitter PA

Caution: Observe precautions when handling because these devices are sensitive to electrostatic discharge

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

★ ORDERING INFORMATION

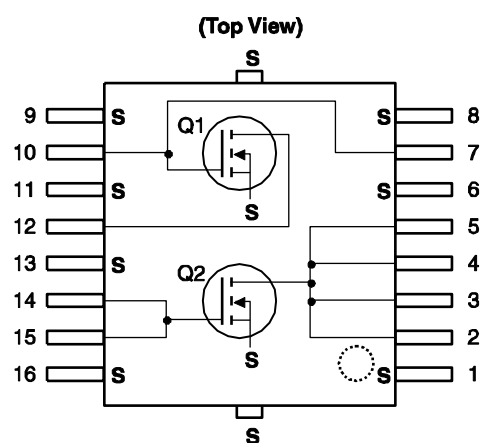
Part Number	Order Number	Package	Marking	Supplying Form
NE55410GR	NE55410GR-T3-AZ	16-pin plastic HTSSOP (Pb-Free) ^{Note}	55410	- Embossed tape 12 mm wide - Pin 1 and 8 indicates pull-out direction of tape - Qty 1 kpcs/reel

Note With regards to terminal solder (the solder contains lead) plated products (conventionally plated), contact your nearby sales office.

Remark To order evaluation samples, contact your nearby sales office.

Part number for sample order: NE55410GR-AZ

PIN CONNECTIONS AND INTERNAL BLOCK DIAGRAM



Pin No.	Pin Name	Pin No.	Pin Name
1	Source	9	Source
2	Drain (Q2)	10	Gate (Q1)
3	Drain (Q2)	11	Source
4	Drain (Q2)	12	Drain (Q1)
5	Drain (Q2)	13	Source
6	Source	14	Gate (Q2)
7	Gate (Q1)	15	Gate (Q2)
8	Source	16	Source

Remark All the terminals of a Q2 connected to a circuit. Backside : Source (S)

ABSOLUTE MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Test Conditions	Ratings	Unit
Drain to Source Voltage	V_{DS}		65	V
Gate to Source Voltage	V_{GS}		± 7	V
Drain Current (Q1)	$I_D (Q1)$		0.25	A
Drain Current (Q2)	$I_D (Q2)$		1.0	A
★ Total Device Dissipation ($T_{case} = 25^\circ\text{C}$)	P_{tot}		40	W
★ Input Power (Q1)	$P_{in (Q1)}$	$f = 2.14 \text{ GHz}$, $V_{DS} = 28 \text{ V}$	0.3	W
★ Input Power (Q2)	$P_{in (Q2)}$	$f = 2.14 \text{ GHz}$, $V_{DS} = 28 \text{ V}$	1.5	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-65 to +150	$^\circ\text{C}$

THERMAL RESISTANCE ($T_A = +25^\circ\text{C}$)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
★ Channel to Case Resistance	$R_{th(ch-c)}$		–	2.5	3.0	$^\circ\text{C/W}$

RECOMMENDED OPERATING CONDITIONS ($T_A = +25^\circ\text{C}$)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	V_{DS}	–	28	30	V
★ Gate to Source Voltage	V_{GS}	2.7	3.3	3.7	V
★ Input Power (Q1), CW	$P_{in(Q1)}$	–	15	23	dBm
★ Input Power (Q2), CW	$P_{in(Q2)}$	–	20	30	dBm

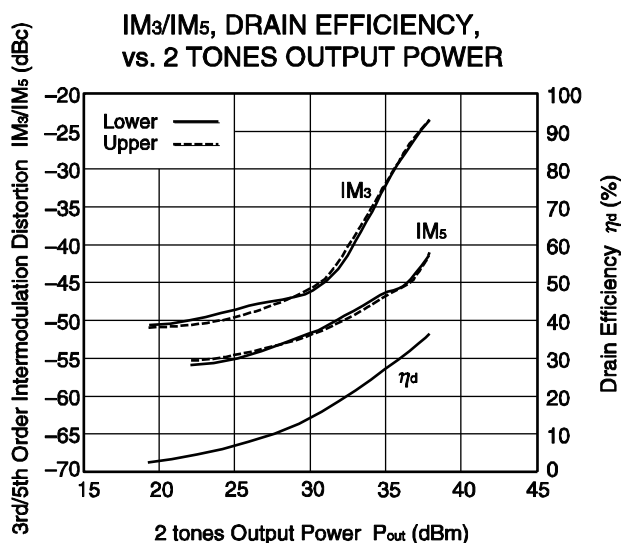
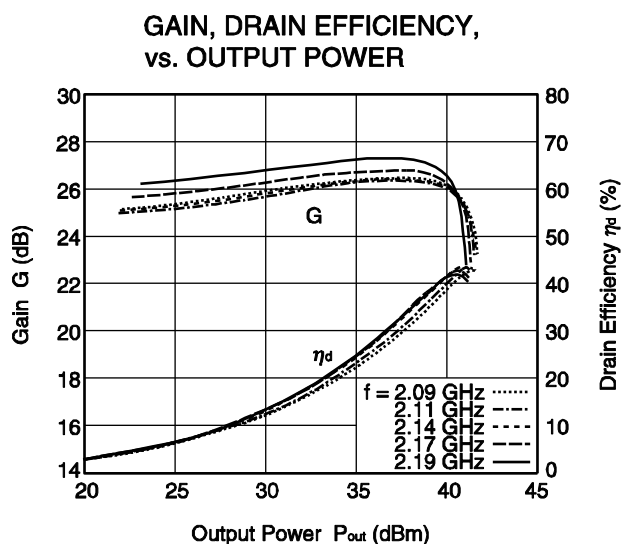
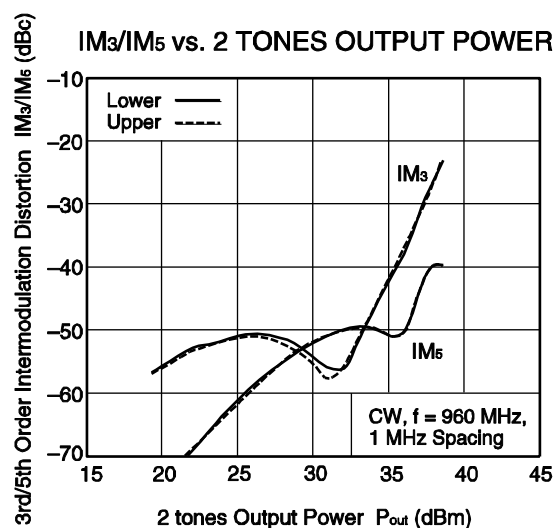
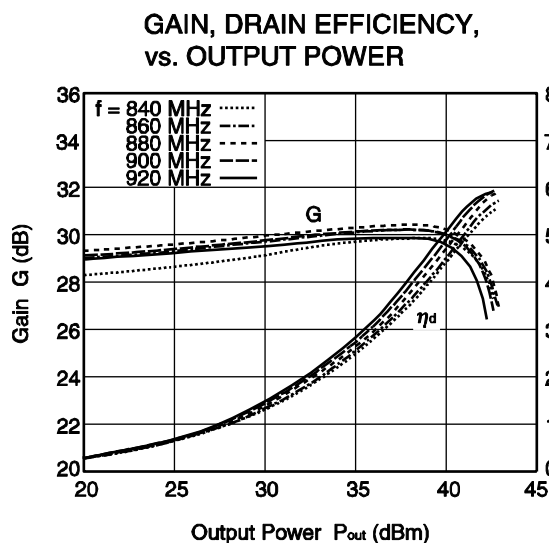
ELECTRICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Q1						
Gate to Source Leak Current	$I_{GSS(Q1)}$	$V_{GSS} = 5\text{V}$	–	–	1	μA
Drain to Source Leakage Current	$I_{DSS(Q1)}$	$V_{DSS} = 65\text{V}$	–	–	1	mA
★ Gate Threshold Voltage	$V_{th(Q1)}$	$V_{DS} = 10\text{V}, I_{DS} = 1\text{mA}$	2.2	2.8	3.4	V
★ Transconductance	$g_{m(Q1)}$	$V_{DS} = 28\text{V}, I_{DS} = 20\text{mA}$	–	0.09	–	S
Drain to Source Breakdown Voltage	$BV_{DSS(Q1)}$	$I_{DSS} = 10\mu\text{A}$	65	75	–	V
Q2						
Gate to Source Leak Current	$I_{GSS(Q2)}$	$V_{GSS} = 5\text{V}$	–	–	1	μA
Drain to Source Leakage Current	$I_{DSS(Q2)}$	$V_{DSS} = 65\text{V}$	–	–	1	mA
★ Gate Threshold Voltage	$V_{th(Q2)}$	$V_{DS} = 10\text{V}, I_{DS} = 1\text{mA}$	2.0	2.6	3.2	V
★ Transconductance	$g_{m(Q2)}$	$V_{DS} = 28\text{V}, I_{DS} = 100\text{mA}$	–	0.45	–	S
Drain to Source Breakdown Voltage	$BV_{DSS(Q2)}$	$I_{DSS} = 10\mu\text{A}$	65	75	–	V

★ RF CHARACTERISTICS (T_A = +25°C)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Q1						
Gain 1 dB Compression Output Power	P _O (1 dB)	f = 2 140 MHz, V _{DS} = 28 V, I _{Dset} = 20 mA	–	35.4	–	dBm
Drain Efficiency	η_d		–	52	–	%
Linear Gain	G _L	P _{in} = 15 dBm	12	13.5	–	dB
Q2						
Gain 1 dB Compression Output Power	P _O (1 dB)	f = 2 140 MHz, V _{DS} = 28 V, I _{Dset} = 100 mA	–	40.4	–	dBm
Drain Efficiency	η_d		–	46	–	%
Linear Gain	G _L	P _{in} = 20 dBm	9.5	11	–	dB
Gain 1 dB Compression Output Power	P _O (1 dB)	f = 1 840 MHz, V _{DS} = 28 V, I _{Dset} = 100 mA	–	40.5	–	dBm
Drain Efficiency	η_d		–	49	–	%
Linear Gain	G _L	P _{in} = 20 dBm	–	14	–	dB
Q1 + Q2						
Gain 1 dB Compression Output Power	P _O (1 dB)	f = 880 MHz, V _{DS} = 28 V, I _{Dset} = 120 mA (Q1 + Q2)	–	41.5	–	dBm
Drain Efficiency	η_d		–	55	–	%
Linear Gain	G _L	P _{in} = 5 dBm	–	30	–	dB
Gain 1 dB Compression Output Power	P _O (1 dB)	f = 2 140 MHz, V _{DS} = 28 V, I _{Dset} = 120 mA (Q1 + Q2)	–	40.0	–	dBm
Drain Efficiency	η_d		34	42	–	%
Output Power	P _{out}	P _{in} = 16 dBm	39	40	–	dB
Linear Gain	G _L	P _{in} = 10 dBm	24	25	–	dB
3rd Order Intermodulation Distortion	IM ₃	f = 2 132.5/2 147.5 MHz, V _{DS} = 28 V, 2 carrier W-CDMA 3GPP, Test Model1, 64DPCH, 67% Clipping, I _{Dset} = 120 mA (Q1 + Q2), Ave P _{out} = 33 dBm	–	–40	–	dBc
Drain Efficiency	η_d		–	21	–	%

★ TYPICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, $V_{DS} = 28\text{ V}$, $I_{Dset} = 120\text{ mA}$, unless otherwise specified)



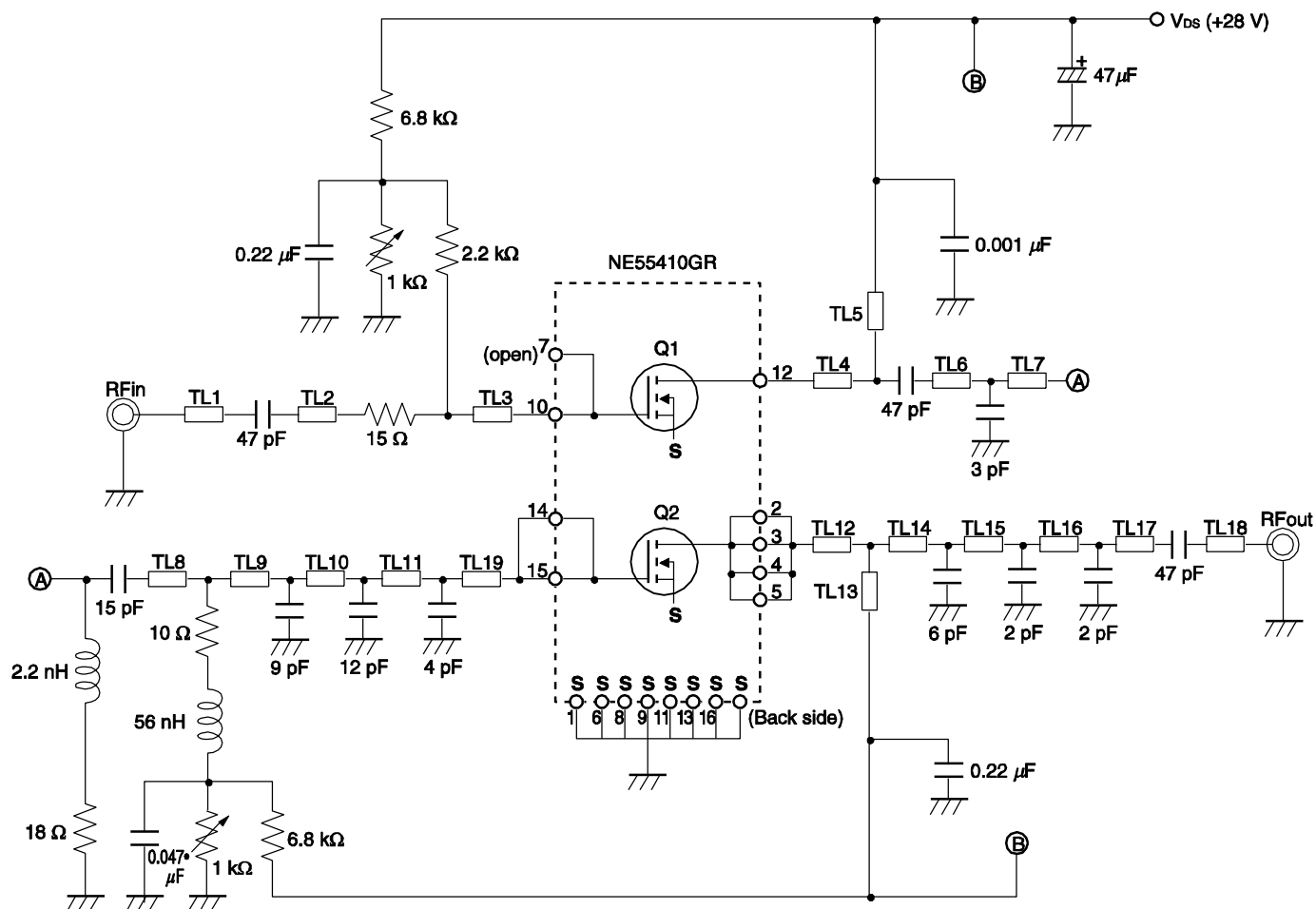
W-CDMA 3GPP, Test Model 1,•
64 DPCH, 67% Clipping,
Center Frequency 2.14GHz,
15 MHz spacing

Remark The graphs indicate nominal characteristics.

S-PARAMETERS

- S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.
- Click here to download S-parameters.
- [RF and Microwave] ® [Device Parameters]
- URL <http://www.necel.com/microwave/en/>

★ EVALUATION CIRCUIT (f = 840 to 960 MHz, $V_{DS} = 28$ V, $I_{Dset} = 120$ mA)

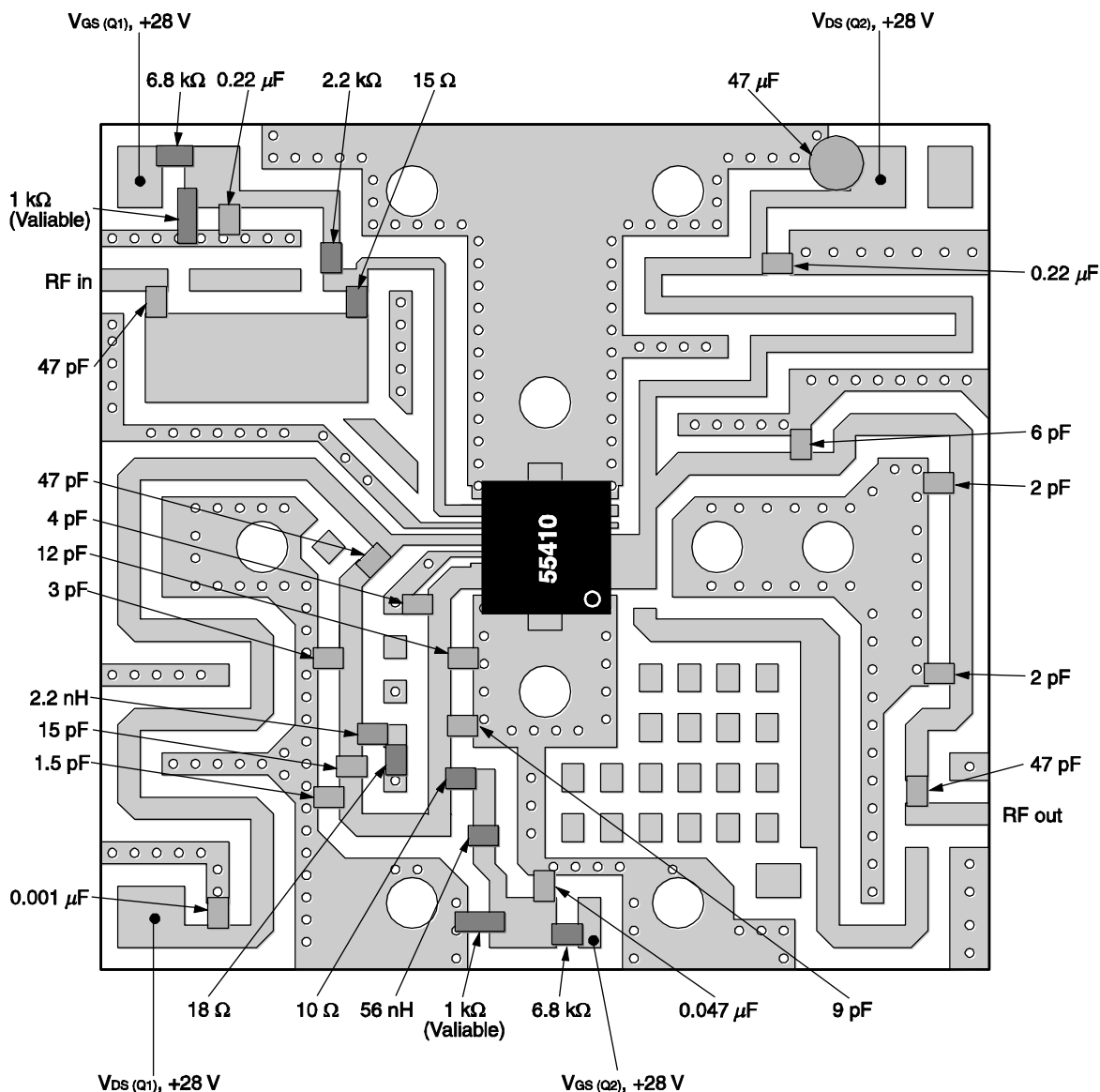


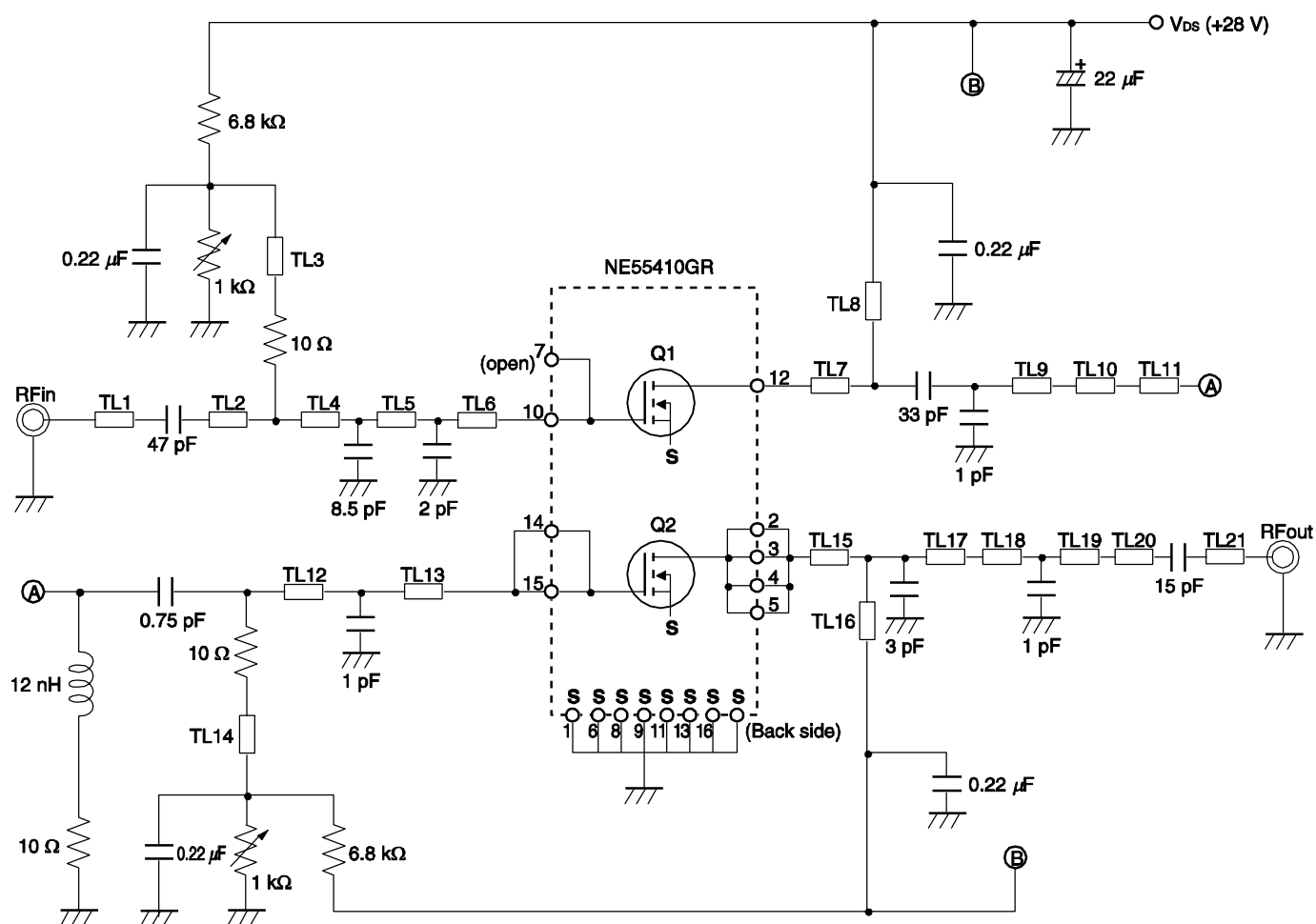
Symbol	Width (mm)	Length (mm)
TL1	1.0	3.0
TL2	4.5	10.0
TL3	0.5	16.0
TL4	0.5	5.0
TL5	1.0	48.0
TL6	1.0	4.0
TL7	1.0	3.0
TL8	1.0	6.0
TL9	1.0	3.0
TL10	1.0	4.0

Symbol	Width (mm)	Length (mm)
TL11	1.0	3.0
TL12	1.0	5.0
TL13	0.8	48.0
TL14	1.0	6.5
TL15	1.0	10.5
TL16	1.0	9.5
TL17	1.0	10.0
TL18	1.0	6.0
TL19	1.0	3.0

The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

★ EVALUATION CIRCUIT ($f = 840$ to 960 MHz, $V_{DS} = 28$ V, $I_{Dset} = 120$ mA)



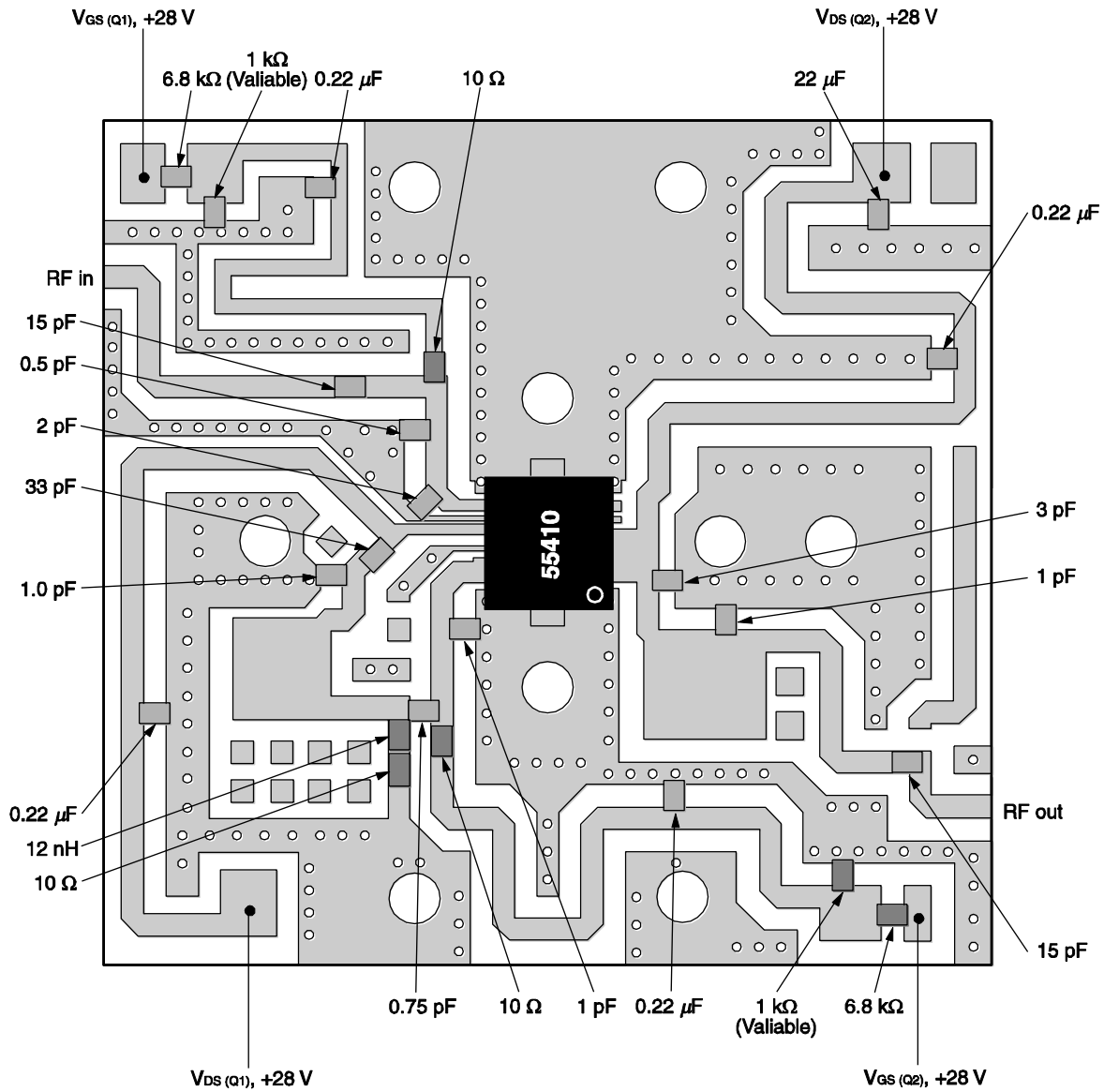
★ EVALUATION CIRCUIT ($f = 2\,090$ to $2\,190$ MHz, $V_{DS} = 28$ V, $I_{Dset} = 120$ mA)

Symbol	Width (mm)	Length (mm)
TL1	1.0	17.0
TL2	1.0	4.0
TL3	1.0	24.5
TL4	1.0	2.5
TL5	1.0	3.0
TL6	0.5	2.5
TL7	0.5	4.5
TL8	1.0	25.5
TL9	1.0	2.5
TL10	4.5	4.5
TL11	1.0	3.5

Symbol	Width (mm)	Length (mm)
TL12	1.0	4.0
TL13	1.0	4.5
TL14	1.0	25.0
TL15	2.5	2.5
TL16	1.0	27.0
TL17	1.0	2.0
TL18	5.0	4.0
TL19	5.0	2.0
TL20	1.0	12.5
TL21	1.0	5.5

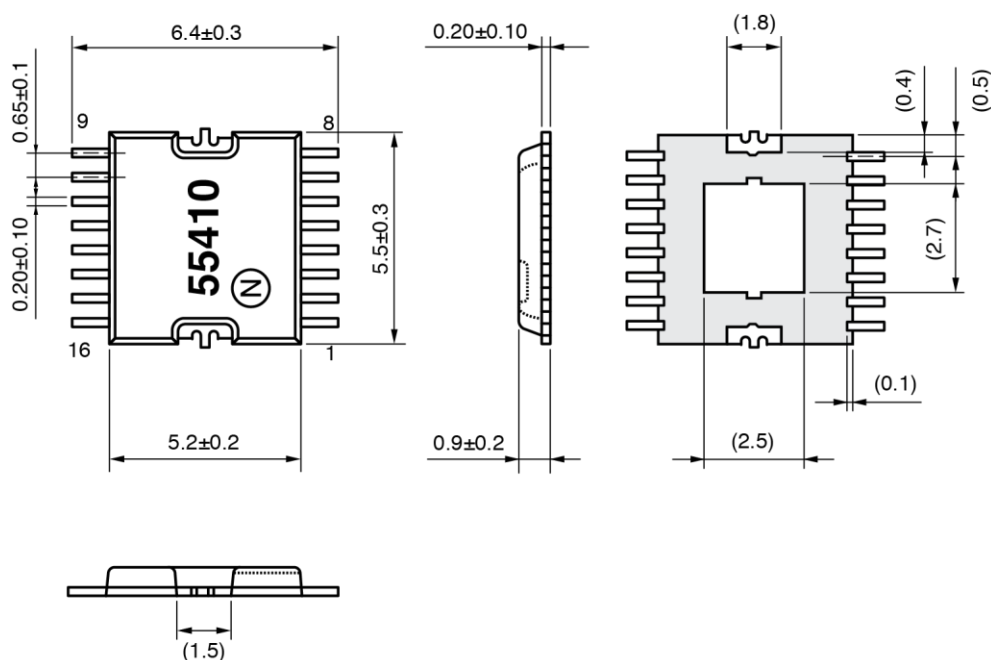
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EVALUATION CIRCUIT ($f = 2\ 090$ to $2\ 190$ MHz, $V_{DS} = 28$ V, $I_{Dset} = 120$ mA)



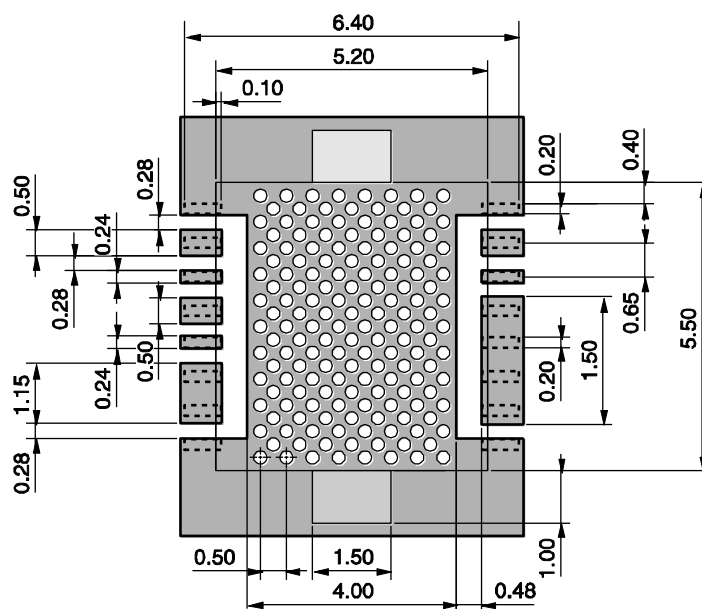
PACKAGE DIMENSIONS

16-PIN PLASTIC HTSSOP (UNIT: mm)



Remark (): Reference value

LAND PATTERN (UNIT: mm)



Remarks1. Via holes : 158 holes

2. Hole size : $\phi 0.25$ mm

3. Min. spacing : 0.354 mm

4.  : Solder resist or etching

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) : 260°C or below Time at peak temperature : 10 seconds or less Time at temperature of 220°C or higher : 60 seconds or less Preheating time at 120 to 180°C : 120±30 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	IR260
Wave Soldering	Peak temperature (molten solder temperature) : 260°C or below Time at peak temperature : 10 seconds or less Preheating temperature (package surface temperature) : 120°C or below Maximum number of flow processes : 1 time Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	WS260
Partial Heating	Peak temperature (terminal temperature) : 350°C or below Soldering time (per side of device) : 3 seconds or less Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	HS350

Caution Do not use different soldering methods together (except for partial heating).